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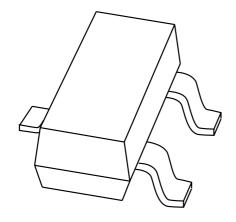
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PBSS5220T 20 V, 2 A PNP low V_{CEsat} (BISS) transistor

Product data sheet 2003 Dec 18



20 V, 2 A PNP low V_{CEsat} (BISS) transistor

PBSS5220T

FEATURES

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- Higher efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- Cost effective alternative to MOSFETs in specific applications.

APPLICATIONS

- Power management
 - DC/DC converters
 - Supply line switching
 - Battery charger
 - LCD backlighting.
- · Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load driver (e.g. relays, buzzers and motors).

DESCRIPTION

PNP BISS transistor in a SOT23 plastic package offering ultra low V_{CEsat} and R_{CEsat} parameters.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PBSS5230T	3F*

Note

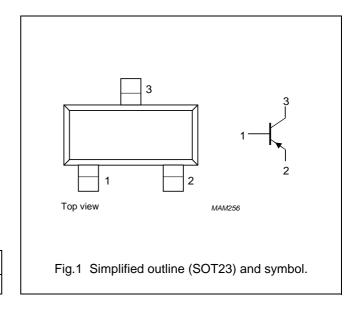
- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-20	V
I _C	collector current (DC)	-2	Α
I _{CM}	peak collector current	-3	Α
R _{CEsat}	equivalent on-resistance 113 m		mΩ

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



ORDERING INFORMATION

TYPE NUMBER	PACKAGE			
TIPE NOMBER	NAME DESCRIPTION VERSION			
PBSS5220T	 plastic surface mounted package; 3 leads 		SOT23	

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-20	V
V_{CEO}	collector-emitter voltage	open base	-	-20	٧
V _{EBO}	emitter-base voltage	open collector	_	- 5	V
I _C	collector current (DC)		_	-2	Α
I _{CM}	peak collector current	single peak	-	-3	Α
I _B	base current (DC)		_	-300	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	300	mW
		T _{amb} ≤ 25 °C; note 2	_	480	mW
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

Notes

- 1. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; standard footprint.
- 2. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

Notes

- 1. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; standard footprint.
- 2. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; mounting pad for collector 1 cm².

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CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -20 \text{ V}; I_E = 0$	_	_	-100	nA
		$V_{CB} = -20 \text{ V}; I_E = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = -100 \text{ mA}$	225	_	_	
		$V_{CE} = -2 \text{ V}; I_{C} = -500 \text{ mA}$	225	-	_	
		$V_{CE} = -2 \text{ V}; I_{C} = -1 \text{ A}; \text{ note } 1$	200	_	_	
		$V_{CE} = -2 \text{ V}; I_{C} = -2 \text{ A}; \text{ note 1}$	150	_	_	
V _{CEsat}	collector-emitter saturation	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	_	-	-80	mV
	voltage	$I_C = -1A$; $I_B = -50 \text{ mA}$	_	-	-150	mV
		$I_C = -2A$; $I_B = -100$ mA; note 1	_	_	-250	mV
		$I_C = -2A$; $I_B = -200$ mA; note 1	_	-	-225	mV
R _{CEsat}	equivalent on-resistance	$I_C = -2 \text{ A}$; $I_B = -200 \text{ mA}$; note 1	_	_	113	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_C = -2 \text{ A}$; $I_B = -100 \text{ mA}$; note 1	_	_	-1.1	V
V _{BEon}	base-emitter turn on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -1 \text{ A}; \text{ note 1}$	-1.2	_	_	V
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -100 \text{ mA}; f = 100 \text{ MHz}$	100	_	_	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	_	50	pF

Note

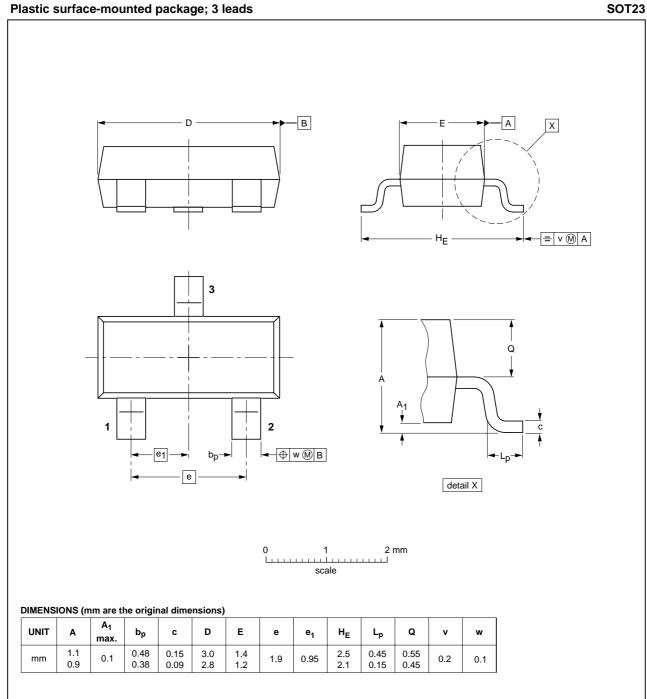
1. Pulse test: $t_p \le 300~\mu s,~\delta \le 0.02.$

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PACKAGE OUTLINE





OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-04-11-04 06-03-16

2003 Dec 18 5

20 V, 2 A PNP low V_{CEsat} (BISS) transistor

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

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